

**EAST Search History****EAST Search History (Prior Art)**

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	("product\$3 same solar adj cells").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/10/15 10:16
L2	28478	product\$3 same solar adj cells	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 10:16
L3	9636	product\$3 same solar adj cells	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 10:16
L4	1	L3 and establish\$3 adj correspondence same wafers same solar adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 10:18
L5	3	L3 and establish\$3 adj correspondence and wafers and solar adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 10:18
L6	106	crystallographic adj structure and wafer\$1 and solar adj cells	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 10:20
L7	5	L6 and matrix same solar adj cells	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 10:21
L8	1	L5 and solar adj cell and produced and treating and silicon adj wafer\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 10:23
L9	507	solar adj cell and produced and treating and silicon adj wafer\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 10:23

L10	34	matrix same solar adj cells and produced and treating and silicon adj wafer\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 10:24
L11	2	L10 and silicon adj wafer\$1 and cutt\$3 and ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 10:26
L12	0	L11 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 10:26
L13	5030	solar adj cells and silicon adj wafer\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 10:36
L14	0	solar adj cells and silicon adj wafer\$1 same solar adj cell adj traceability	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 10:36
L15	1	solar adj cells and silicon adj wafer\$1 and solar adj cell adj traceability	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 10:36
L16	9636	product\$3 same solar adj cells	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 10:38
L17	8	L16 and crystallographic adj structure and wafer\$1 and solar adj cells	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 10:39
L18	18	solar adj cells and silicon adj wafer\$1 and traceability	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 10:48
L19	5	L18 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 10:48
L20	72405	(compar\$3 or match\$3)and wafer\$1 and(solar adj cells or cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 10:57

L21	2509	(compar\$3 or match\$3) same wafer\$1 same(solar adj cells cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 10:57
L22	3	L21 and matrix same solar adj cells and produced and treating and silicon adj wafer\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 10:58
L23	0	L22 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 10:58
L24	1	image\$3 adj device and crystallographic adj structure and wafer and cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 11:02
L25	429	crystallographic adj structure and wafer and cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 11:03
L26	5	L25 and(compar\$3 or match\$3) same wafer\$1 same(solar adj cells or cell or matrix)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 11:03
L27	3	L26 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 11:03
L28	0	L27 and(image\$3 adj device or camera or ccd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 11:23
L29	106	L25 and(image\$3 adj device or camera or ccd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 11:23
L30	32	L29 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 11:23
L31	0	L30 and(compar\$3 or match\$3) same wafer\$1 same(solar adj cells or cell or matrix)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 11:23

L32	27	L30 and(compar\$3 or match\$3) and wafer\$1 and(solar adj cells or cell or matrix)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 11:24
L33	0	L32 and matrix same solar adj cells and produced and treating and silicon adj wafer\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 11:24
L34	1	L32 and matrix and solar adj cells and produced and treating and silicon adj wafer\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 11:24
L35	345	L25 and(defects or variances or voids or defects or stacking adj faults or inclusions or impurities or grain or crystal adj boundaries or breakage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 11:36
L36	86	L35 and(image\$3 adj device or camera or cod)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 11:37
L37	78	L36 and(compar\$3 or match\$3) and wafer\$1 and(solar adj cells or cell or matrix)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 11:37
L38	0	L37 and defect same breakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 11:38
L39	6	L37 and defect and breakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 11:38
L40	25	L37 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 11:39
L41	0	L25 and(compar\$3 or match\$3) and wafer\$1 and(solar adj cells or cell or matrix)and(software or program)and image adj recognition and detect adj defect and breakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 11:44

L42	0	(compar\$3 or match\$3)and wafer\$1 and(solar adj cells or cell or matrix)and(software or program)and image adj recognition and detect adj defect and breakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 11:44
L43	0	L25 and(software or program) and image adj recognition and detect adj defect and breakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 11:46
L44	1	(software or program)and image adj recognition and detect adj defect and breakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 11:46
L45	3350	crystallographic adj structure and(produc\$4 or obtaining)and (cell adj image or cells or cell or wafer or memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 11:47
L46	0	L45 and(software or program) and image adj recognition and detect adj defect and breakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 11:48
L47	0	L45 and image adj recognition and detect adj defect and breakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 11:48
L48	0	L25 and image adj recognition and detect adj defect and breakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/15 11:48
S1	2124	sheela chawan.Xa.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/09 15:40
S2	2338	sheela chawan.Xp.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/09 15:46
S3	2	S1 and wafer adj polishing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/09 15:46
S4	2	S2 and wafer adj polishing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/09 15:47

S5	22	S1 and wafer adj inspection	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/09 15:48
S6	22	S2 and wafer adj inspection	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/09 15:48
S7	156	wafer adj pad and inspection	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/09 16:05
S8	156	wafer adj pad and inspection	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:04
S9	27	S8 and notch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:04
S10	337122	crystallographic adj structure and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:09
S11	966	crystallographic adj structure and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:09
S12	191	crystallographic adj structure same wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:09
S13	150	S12 and (@ad<"20040202" or @rlad<"20040202" or @prad<"20040202" or @ptad<"20040202")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:21
S14	117	S12 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:21
S15	16	S14 and(solar adj cell or cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:22

S16	16	S15 and (compar\$3 or match\$3) and wafer and(solar adj cell or cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:23
S17	41	crystallographic adj structure and wafer and ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:39
S18	5	S17 and(compar\$3 or match\$3) and wafer and(solar adj cell or cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:40
S19	4	S18 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:40
S20	110	((("4352948") or ("6161054") or ("5203005") or ("5287472") or ("5292677") or ("5485097") or ("6243308") or ("4435498") or ("4471483") or ("4493055") or ("4519035") or ("4543444") or ("4898835") or ("4999689") or ("5019736") or ("5024972") or ("5252507") or ("5265847") or ("5315130") or ("5362666") or ("5393617") or ("5478363") or ("5491665") or ("5536964") or ("5552243") or ("5619419") or ("5624771") or ("5656392") or ("5657284") or ("5698453") or ("5698342") or ("5716459") or ("5808947") or ("5821160") or ("5851693") or ("5926419") or ("6040912") or ("RE36644") or ("6046078") or ("6140140") or ("6161213") or ("6225167") or ("6330819") or ("4304641") or ("4338480") or ("4353160") or ("4385198") or ("4400221") or ("4400868") or ("pn.")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/03/10 16:43
S21	106	S20 and (@ad<"20040202" or @lad<"20040202" or @prad<"20040202" or @ptad<"20040202")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:43
S22	106	S20 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:43

S23	0	S22 and crystallographic adj structure and wafer and ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:44
S24	0	S22 and crystallographic adj structure and wafer and ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 16:46
S25	5	S22 and inspect\$3 and (crystallographic adj structure or wafer or ingot or cells or cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:05
S26	4	S25 and (compar\$3 or match\$3) and(solar adj cell or cell crystallographic adj structure or wafer or ingot or cells or cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:06
S27	4	S26 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:07
S28	4742	crystallographic adj structure	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:10
S29	4328355	(wafer\$1 or semiconductor or solar adj cell or cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:11
S30	98638	S29 and inspect\$3 and(cells or cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:20
S31	153527	S29 and inspect\$3 and(cells or cell or wafer or memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:21
S32	4742	crystallographic adj structure	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:22
S33	632	S31 and S32	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:27

S34	1	S33 and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:28
S35	3	inspect\$3 and solar adj cell and matrix and convert\$3 and electricity and solar adj cell and treating and silicon adj wafers and ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:32
S36	2	S35 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:33
S37	1	S35 and (compar\$3 or match\$3) and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:39
S38	1	S32 and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:40
S39	17	S29 and (compar\$3 or match\$3) and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:40
S40	3	S39 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:41
S41	1	S39 and crystallographic adj structure	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:51
S42	1	S39 and crystallographic adj structure and wafer adj structure and manufactured adj cell and crystallographic adj image and information and sufficient adj establish and correspondence and cell and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:58
S43	1	S39 and crystallographic adj structure and wafer adj structure and manufactured adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:59

S44	1	crystallographic adj structure and wafer adj structure and manufactured adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 17:59
S45	2	S29 and crystallographic adj structure and manufactured adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:00
S46	0	S45 and @adj<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:01
S48	607	S32 and inspect\$3 and(cells or cell or memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:06
S49	1	S48 and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:06
S50	587	S48 and(compar\$3 or match\$3) and (memory or cell or memory adj cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:07
S51	1	S48 and(compar\$3 or match\$3) same(memory or cell or memory adj cell)same wafer\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:08
S52	1	S50 and crystallographic adj structure and wafer adj structure and manufactured adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:09
S53	1	S50 and wafer adj structure and manufactured adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:09
S54	1	S50 and manufactured adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:10
S55	297	S50 and @adj<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:10

S56	12	S55 and (compar\$3 or match\$3) and wafer and(solar adj cell or cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:11
S57	13	S55 and inspect\$3 and wafer\$1 and(cells or cell or memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:12
S58	0	S55 and inspect\$3 adj wafer\$1 same(cells or cell or memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:13
S59	0	S55 and inspect\$3 adj wafer\$1 and(cells or cell or memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:13
S60	3559	S28 and(wafer\$1 or semiconductor or solar adj cell or cell or memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:14
S61	2	S60 and manufactured adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:14
S62	0	S61 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:14
S63	2	S32 and manufactured adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:15
S64	1818	S32 and(wafer\$1 or semiconductor or memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:16
S65	237	S32 and(wafer\$1 or semiconductor or memory)and inspect\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:16
S66	119	S65 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:16

S67	12	S66 and(compar\$3 or match\$3) and wafer and(solar adj cell or cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:19
S68	38	S32 and inspect\$3 and(compar \$3 or match\$3)and wafer and (solar adj cell or cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:28
S69	41	S32 and inspect\$3 and(compar \$3 or match\$3)and wafer and (solar adj cell or cell or memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:29
S70	13	S69 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:29
S71	85837	analyze\$3 and(crystalline or crystallographic adj structure)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:35
S72	18	S71 and manufactured adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:36
S73	1	S72 and(wafer\$1 or semiconductor or memory)and inspect\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:36
S74	1	inspect\$3 and photovoltaic adj area and manufactured and crystalline adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:43
S75	0	S74 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:44
S76	0	S72 and(imaging or ccd or camera or CMOS or IR)and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:46
S77	0	S71 and(imaging or ccd or camera or CMOS or IR)and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:47

S78	31037	S71 and(imaging or ccd or camera or CMOS or IR)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:47
S79	8	S78 and manufactured adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:47
S80	2	S79 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:48
S81	2106	S78 and(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit) and inspect\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:51
S82	45	S81 and(compar\$3 or match\$3) same(memory or cell or memory adj cell) same wafer\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:52
S83	18	S82 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 18:52
S84	25	S17 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 19:17
S85	5	S72 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 19:48
S86	118795	(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit) and inspect\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 19:49
S87	9	S86 and(imaging or ccd or camera or CMOS or IR)and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 19:49
S88	1	S87 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 19:49

S89	533	crystallographic adj structure and(wafer or ingot)and section	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 20:15
S90	161	S89 and analyz\$3 and (crystalline or crystallographic adj structure)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 20:16
S91	0	S89 and analyz\$3 and (crystalline or crystallographic adj structure) same ignot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 20:16
S92	0	S90 and(imaging or cod or camera or CMOS or IR)and wafer adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 20:17
S93	120	S90 and(imaging or cod or camera or CMOS or IR)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 20:17
S94	48	S93 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 20:22
S95	0	S93 and etching and texturisation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 20:59
S96	7	(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)and etching and texturisation and inspect\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:00
S97	2	S96 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:00
S98	0	S97 and(compar\$3 or match\$3) same(memory or cell or memory adj cell or die)same wafer\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:01
S99	0	S97 and(compar\$3 or match\$3) and(memory or cell or memory adj cell or die)and wafer\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:01

S100	2	S97 and(memory or cell or memory adj cell or die)and wafer \$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:01
S101	161	S89 and S90	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:05
S102	0	S101 and(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)and etching and texturisation and inspect\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:06
S103	0	S101 and etching and texturisation and inspect\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:06
S104	0	S101 and etching and texturisation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:07
S105	1	S89 and etching and texturisation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:07
S106	20	S89 and solar adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:08
S107	8	S106 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:08
S108	2468	Ingot and production adj process	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:10
S109	523	S108 and wafer\$3 and production adj process	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:11
S110	128	S109 and cell and production adj process	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:11

S111	1	S110 and wafer adj position\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:12
S112	75	S110 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:13
S113	0	S112 and cell adj inspect\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:13
S114	75	S112 and(memory or cell or memory adj cell or die)and wafer \$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:14
S115	0	S114 and(imaging or ccd or camera or CMOS or IR)and wafer adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:14
S116	12	S114 and(imaging or ccd or camera or CMOS or IR)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:14
S117	10	S116 and(compar\$3 or match\$3) and(memory or cell or memory adj cell or die)and wafer\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:15
S118	10	S117 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/10 21:15
S119	93	measur\$3 and polycrystalline adj wafer\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:04
S120	63	photovoltaic adj devices and (slicing or dice\$3 or diced)and ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:05
S121	0	defect adj characteriz\$3 and classificat\$3 and crystal adj growth and ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:07

S122	54	defect and classificat\$3 and crystal adj growth and ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:08
S123	0	(defects or grain adj boundaries) and processing adj wafer\$1 and classificat\$3 and crystal adj growth and ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:09
S124	75	(defects or grain adj boundaries) and processing adj wafer\$1 and crystal adj growth and ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:10
S125	3	S119 and S120	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:10
S126	0	S124 and S125	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:11
S127	0	S125 and(defects or grain adj boundaries)and crystal adj growth and ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:11
S128	0	S125 and(defects or grain adj boundaries)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:12
S129	0	S125 and defects and crystal adj growth and ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:12
S130	10	S120 and(imaging or cod or camera or CMOS or IR)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:15
S131	3	S130 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:16
S132	0	S120 and inspect\$3 adj defects and crystal adj growth and ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:29

S133	0	S120 and inspect\$3 and defects and crystal adj growth and ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:29
S134	4	S120 and inspect\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:30
S135	1	S134 and(defects or grain adj boundaries)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:30
S136	0	S135 and @ad<"2004040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:30
S137	55	S120 and(defects or variances or voids or defects or stacking adj faults or inclusions or impurities or grain or crystal adj boundaries)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:35
S138	1	S137 and(imaging or cod or camera or CMOS or IR)and surface adj wafer\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:35
S139	0	S138 and @ad<"2004040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:36
S140	55	S120 and S137	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:36
S141	20	S140 and @ad<"2004040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:36
S142	13	S141 and(compar\$3 or match\$3) and(wafer or ingot or cells or cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:44
S143	11	S141 and(compar\$3 or match\$3) same(wafer or ingot or cells or cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:46

S144	11	S143 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:46
S145	0	S141 and(imaging or ccd or camera or CMOS or IR)and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:49
S146	0	S141 and(imaging or ccd or camera or CMOS or IR)and wafer adj image and cell adj image and(compar\$3 or match \$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:50
S147	0	S137 and(imaging or ccd or camera or CMOS or IR)and wafer adj image and cell adj image and(compar\$3 or match \$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:50
S148	0	S120 and(imaging or ccd or camera or CMOS or IR)and wafer adj image and cell adj image and(compar\$3 or match \$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:51
S149	0	S120 and(imaging or ccd or camera or CMOS or IR)and wafer adj image and cell adj image and(compar\$3 or match \$3)and surface adj wafer\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:51
S150	0	S119 and(imaging or ccd or camera or CMOS or IR)and wafer adj image and cell adj image and(compar\$3 or match \$3)and surface adj wafer\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:52
S151	0	S124 and(imaging or ccd or camera or CMOS or IR)and wafer adj image and cell adj image and(compar\$3 or match \$3)and surface adj wafer\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:52
S152	0	S120 and(imaging or ccd or camera or CMOS or IR)and (compar\$3 or match\$3)and surface adj wafer\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:53
S153	5	(imaging or ccd or camera or CMOS or IR)and(compar\$3 or match\$3)and photovoltaic adj devices and(slicing or dice\$3 or diced) and ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:54
S154	2	S153 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:54

S155	2	S154 and(defects or variances or voids or defects or stacking adj faults or inclusions or impurities or grain or crystal adj boundaries)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 10:55
S156	4	S120 and(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit) and inspect\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:04
S157	10	S119 and(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit) and inspect\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:04
S158	0	S156 and(imaging or cod or camera or CMOS or IR)and wafer adj image and cell adj image and(compar\$3 or match \$3)and surface adj wafer\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:04
S159	0	S156 and(imaging or cod or camera or CMOS or IR)and wafer adj image and cell adj image and(compar\$3 or match \$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:05
S160	0	S157 and(imaging or cod or camera or CMOS or IR)and wafer adj image and cell adj image and(compar\$3 or match \$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:05
S161	0	S157 and(imaging or cod or camera or CMOS or IR)and (compar\$3 or match\$3)and photovoltaic adj devices and (slicing or dice\$3 or diced)and ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:05
S162	0	S157 and(imaging or cod or camera or CMOS or IR)and (compar\$3 or match\$3)and (cell adj solar or cell or memory or wafer\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:06
S163	4	S157 and(imaging or cod or camera or CMOS or IR)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:06
S164	4	S163 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:06
S165	1	S164 and(defects or variances or voids or defects or stacking adj faults or inclusions or impurities or grain or crystal adj boundaries)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:07

S166	0	S119 and produc\$4 and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:16
S167	0	S120 and produc\$4 and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:16
S168	0	S122 and produc\$4 and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:16
S169	0	S122 and(produc\$4 or obtaining) and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:16
S170	0	S157 and(produc\$4 or obtaining) and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:17
S171	0	S153 and(produc\$4 or obtaining) and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:17
S172	0	S155 and(produc\$4 or obtaining) and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:17
S173	1	crystallographic adj structure and(produc\$4 or obtaining)and wafer adj image and cell adj image and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:18
S174	1	crystallographic adj structure and(produc\$4 or obtaining)and wafer adj image and(cell adj image or cells or cell or wafer or memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:20
S175	3130	crystallographic adj structure and(produc\$4 or obtaining) and (cell adj image or cells or cell or wafer or memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:20
S176	2	S175 and photovoltaic adj devices and(slicing or dice\$3 or diced)and ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:21

S177	2	S176 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:21
S178	0	S177 and(imaging or ccd or camera or CMOS or IR or image)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:31
S179	1586	S175 and(imaging or ccd or camera or CMOS or IR or image)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:31
S180	0	S179 and photovoltaic adj devices and(slicing or dice\$3 or diced)and ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:32
S181	0	S179 and photovoltaic adj devices and(slicing or dice\$3 or diced)and (ingot or wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)and inspect\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:33
S182	2	S175 and photovoltaic adj devices and(slicing or dice\$3 or diced)and (ingot or wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:34
S183	2	S182 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:34
S184	2	S183 and(defects or variances or voids or defects or stacking adj faults or inclusions or impurities or grain or crystal adj boundaries or grain adj boundaries)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 11:37
S185	850	wafer\$1 adj identification	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/12 12:14
S186	1	S185 and etching and texturisation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/12 12:14

S187	348	S185 and (etching or texturisation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/12 12:15
S188	48	wafer\$1 adj identification same (imaging or ccd or camera or CMOS or IR)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/12 12:16
S189	12	S188 and (etching or texturisation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/12 12:16
S190	0	S189 and phosphorus adj doping	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/12 12:16
S191	0	S189 and phosphorus and doping	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/12 12:17
S192	8	S189 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/12 12:17
S193	0	S188 and phosphorus adj doping	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/12 12:21
S194	1323	phosphorus adj doping	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/12 12:21
S195	872	S194 and (etching or texturisation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/12 12:21
S196	1	S195 and wafer\$1 adj identification and(imaging or ccd or camera or CMOS or IR)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/12 12:21
S197	29	S195 and identification and (imaging or ccd or camera or CMOS or IR)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/12 12:23

S198	16	S197 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/12 12:23
S199	0	S198 and edge adj etching	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/12 12:23
S200	14	S198 and edge and etching	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/12 12:23
S201	0	S200 and oxide adj removal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/12 12:24
S202	10	S200 and oxide and removal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/12 12:24
S203	1323	phosphorus adj doping	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/12 12:25
S204	898	S203 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/12 12:25
S205	8	S204 and oxide adj removal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/12 12:26
S206	0	S205 and antireflective adj coating	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/12 12:26
S207	0	S205 and screen adj print	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/12 12:27
S208	1	S203 and inspect\$3 adj wafer\$1 and(cells or cell or memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/12 12:28

S209	1	S203 and wafer\$1 adj identification and(imaging or ccd or camera or CMOS or IR)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/12 12:29
S210	566	wafer\$1 and screen adj print	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/12 12:29
S211	15	S210 and antireflective adj coating	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/12 12:30
S212	2	S211 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/12 12:30
S213	0	S198 and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/12 12:34
S214	1	S203 and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/12 12:34
S215	1	determining adj quality and wafer adj production and cell adj production and process	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/12 12:36
S216	12	quality and wafer adj production and cell adj production and process	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/12 12:37
S217	1	S216 and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/12 12:37
S218	2	S216 and identification and (imaging or ccd or camera or CMOS or IR)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/12 12:37
S219	0	S218 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/12 12:38

S220	8	S216 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/12 12:40
S221	22	Ingot adj production and wafer adj production	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/16 11:52
S222	10	S221 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/16 11:53
S223	0	Ingot adj production and wafer adj production same(slicing or dice\$3 or diced)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/16 12:07
S224	6	Ingot adj production same (slicing or dice\$3 or diced)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/16 12:07
S225	4	S224 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/16 12:07
S226	0	S224 and cell adj inspect\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/16 12:12
S227	1	S221 and cell adj inspect\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/16 12:12
S228	0	cell adj inspect\$3 and wafer adj production same(slicing or dice \$3 or diced)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/16 12:14
S229	0	cell adj inspect\$3 and wafer adj production and(slicing or dice\$3 or diced)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/16 12:14
S230	22	cell adj inspect\$3 and(slicing or dice\$3 or diced)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/16 12:14

S231	6	S230 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/16 12:18
S232	0	cell adj inspect\$3 and imaging and(slicing or dice\$3 or diced)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/16 13:05
S233	140	image\$3 and cell adj image and (slicing or dice\$3 or diced)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/16 13:06
S234	0	S233 and Ingot adj production same(slicing or dice\$3 or diced)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/16 13:06
S235	0	S233 and Ingot adj production and(slicing or dice\$3 or diced)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/16 13:07
S236	2	"6140140".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/16 14:52
S237	23	cell adj inspect\$3 and(slicing or dice\$3 or diced)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:19
S238	6	S237 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:19
S239	3	S238 and (breakage or damage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:21
S240	64	photovoltaic adj devices and (slicing or dice\$3 or diced)and ingot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:23
S241	55	S240 and(defects or variances or voids or defects or stacking adj faults or inclusions or impurities or grain or crystal adj boundaries)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:23

S242	20	S241 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:24
S243	3	S242 and breakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:25
S244	2	S237 and(compar\$3 or match\$3) and breakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:36
S245	1	S244 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:37
S246	4764	crystallographic adj structure	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:37
S247	110	S246 and(compar\$3 or match\$3) and breakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:37
S248	65	S247 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:38
S249	2	"7144457".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:44
S250	0	S249 and(compar\$3 or match\$3) and breakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:44
S251	0	S249 and breakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:44
S252	2	"6465781".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:45

S253	0	S252 and breakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:45
S254	4764	crystallographic adj structure	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:46
S255	1	S254 and wafer adj image and cell adj image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:46
S256	110	((("4352948") or ("6161054") or ("5203005") or ("5287472") or ("5292677") or ("5485097") or ("6243308") or ("4435498") or ("4471483") or ("4493055") or ("4519035") or ("4543444") or ("4898835") or ("4999689") or ("5019736") or ("5024972") or ("5252507") or ("5265847") or ("5315130") or ("5362666") or ("5393617") or ("5478363") or ("5491665") or ("5536964") or ("5552243") or ("5619419") or ("5624771") or ("5656392") or ("5657284") or ("5698453") or ("5698342") or ("5716459") or ("5808947") or ("5821160") or ("5851693") or ("5926419") or ("6040912") or ("RE36644") or ("6046078") or ("6140140") or ("6161213") or ("6225167") or ("6330819") or ("4304641") or ("4338480") or ("4353160") or ("4385198") or ("4400221") or ("4400868") or ("").pn."))..PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/03/27 17:47
S257	106	S256 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:47
S258	5	S257 and inspect\$3 and (crystallographic adj structure or wafer or ingot or cells or cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:47
S259	4	S258 and(compar\$3 or match\$3) and(solar adj cell or cell crystallographic adj structure or wafer or ingot or cells or cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:47

S260	5	S257 and inspect\$3 and (crystallographic adj structure or wafer or ingot or cells)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:47
S261	0	S260 and(compar\$3 or match\$3) and breakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:48
S262	0	S260 and breakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:48
S263	142	image\$3 and cell adj image and (slicing or dice\$3 or diced)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:48
S264	6	S263 and(compar\$3 or match\$3) and breakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:48
S265	2	S264 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:49
S266	110	S246 and(compar\$3 or match\$3) and breakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:50
S267	65	S266 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:50
S268	66	S267 cell adj image and wafer adj image and(compar\$3 or match\$3)and breakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:51
S269	66	S267 cell adj image and wafer adj image same(compar\$3 or match\$3)same breakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:51
S270	65	S269 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:51

S271	2	"5667597".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:55
S272	0	S271 and breakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:55
S273	2	"6316832".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:56
S274	2	S273 and breakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:56
S275	4764	S254 cell adj image and wafer adj image and(compar\$3 or match\$3)and breakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:57
S276	1	S254 and cell adj image and wafer adj image and(compar\$3 or match\$3)and breakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:58
S277	2	"5716459".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:58
S278	0	S277 and breakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:59
S279	2	"5153444".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:59
S280	0	S279 and breakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 17:59
S281	535	crystallographic adj structure and(wafer or ingot)and section	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 18:01

S282	1	S281 and cell adj image same wafer adj image same(compar \$3 or match\$3) same breakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 18:01
S283	2	"7144457".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 18:02
S284	0	S283 and(breakage or damaged)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 18:03
S285	42	S254 and inspect\$3 and(compar \$3 or match\$3) and wafer and (solar adj cell or cell or memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 18:08
S286	13	S285 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 18:08
S287	0	S286 and breakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 18:08
S288	535	crystallographic adj structure and(wafer or ingot)and section	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 18:09
S289	162	S288 and analyz\$3 and (crystalline or crystallographic adj structure)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 18:09
S290	120	S289 and(imaging or cod or camera or CMOS or IR)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 18:09
S291	48	S290 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 18:09
S292	0	S291 and(breakage or damaged)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 18:09

S293	2491	ingot and production adj process	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 18:11
S294	525	S293 and wafer\$3 and production adj process	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 18:11
S295	128	S294 and cell and production adj process	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 18:11
S296	75	S295 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 18:11
S297	75	S296 and(memory or cell or memory adj cell or die)and wafer\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 18:11
S298	12	S297 and(imaging or ccd or camera or CMOS or IR)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 18:11
S299	10	S298 and(compar\$3 or match\$3) and(memory or cell or memory adj cell or die)and wafer\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 18:11
S300	10	S299 and @ad<"20040202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 18:11
S301	6	S300 and(breakage or damaged)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 18:11
S302	2	S300 and breakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 18:17
S303	2	"6140140".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 18:31

S304	1	S303 and memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 18:32
S305	2	"5757474".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 21:51
S306	0	S305 and(breakage or damage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 21:56
S307	2	"5757474".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/29 10:00
S308	2	"6482661".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/29 10:01
S309	111	((("4352948") or ("6161054") or ("5203005") or ("5287472") or ("5292677") or ("5485097") or ("6243308") or ("4435498") or ("4471483") or ("4493055") or ("4519035") or ("4543444") or ("4898835") or ("4999689") or ("5019736") or ("5024972") or ("5252507") or ("5265847") or ("5315130") or ("5362666") or ("5393617") or ("5478363") or ("5491665") or ("5536964") or ("5552243") or ("5619419") or ("5624771") or ("5656392") or ("5657284") or ("5698453") or ("5698342") or ("5716459") or ("5808947") or ("5821160") or ("5851693") or ("5926419") or ("6040912") or ("RE36644") or ("6046078") or ("6140140") or ("6161213") or ("6225167") or ("6330819") or ("4304641") or ("4338480") or ("4353160") or ("4385198") or ("4400221") or ("4400868") or ("").pn.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/03/29 10:02

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